

FIGURE 1
(PRIOR ART)

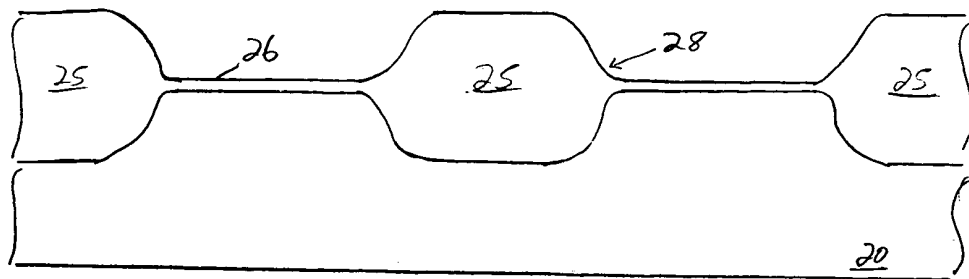


FIGURE 2
(PRIOR ART)

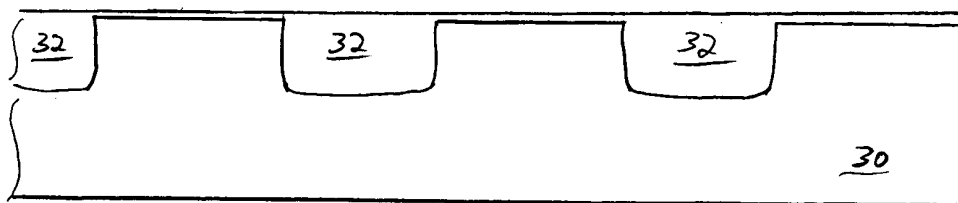


FIGURE 3
(PRIOR ART)

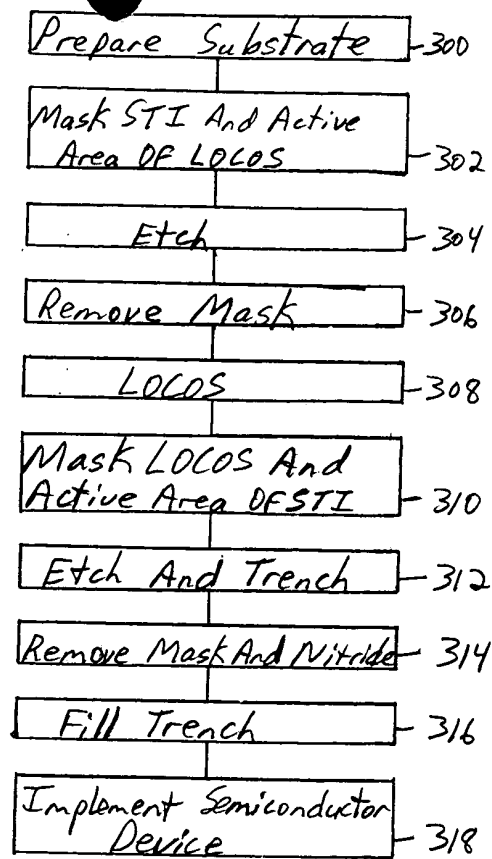


FIGURE 4

650250"663760

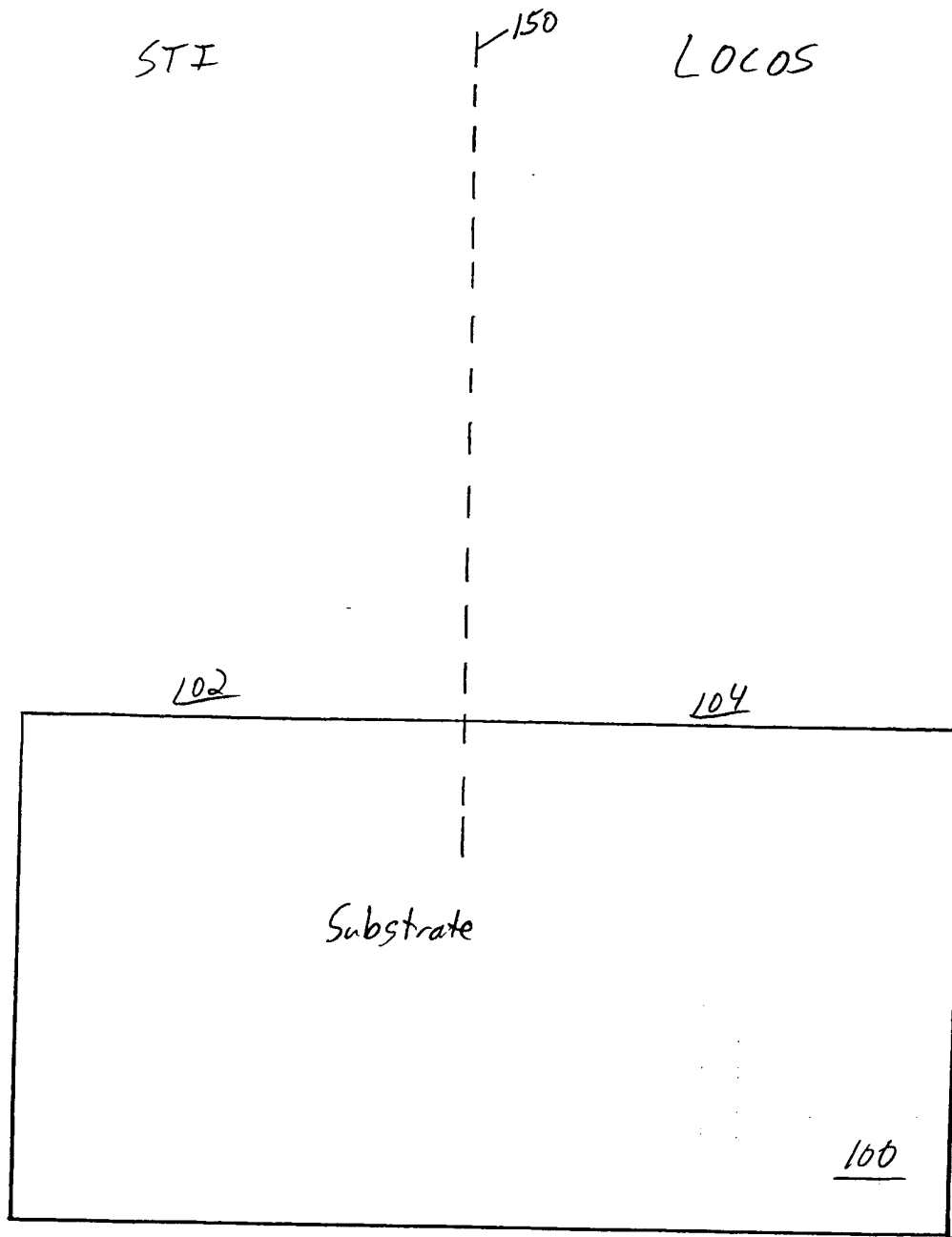


FIGURE 5

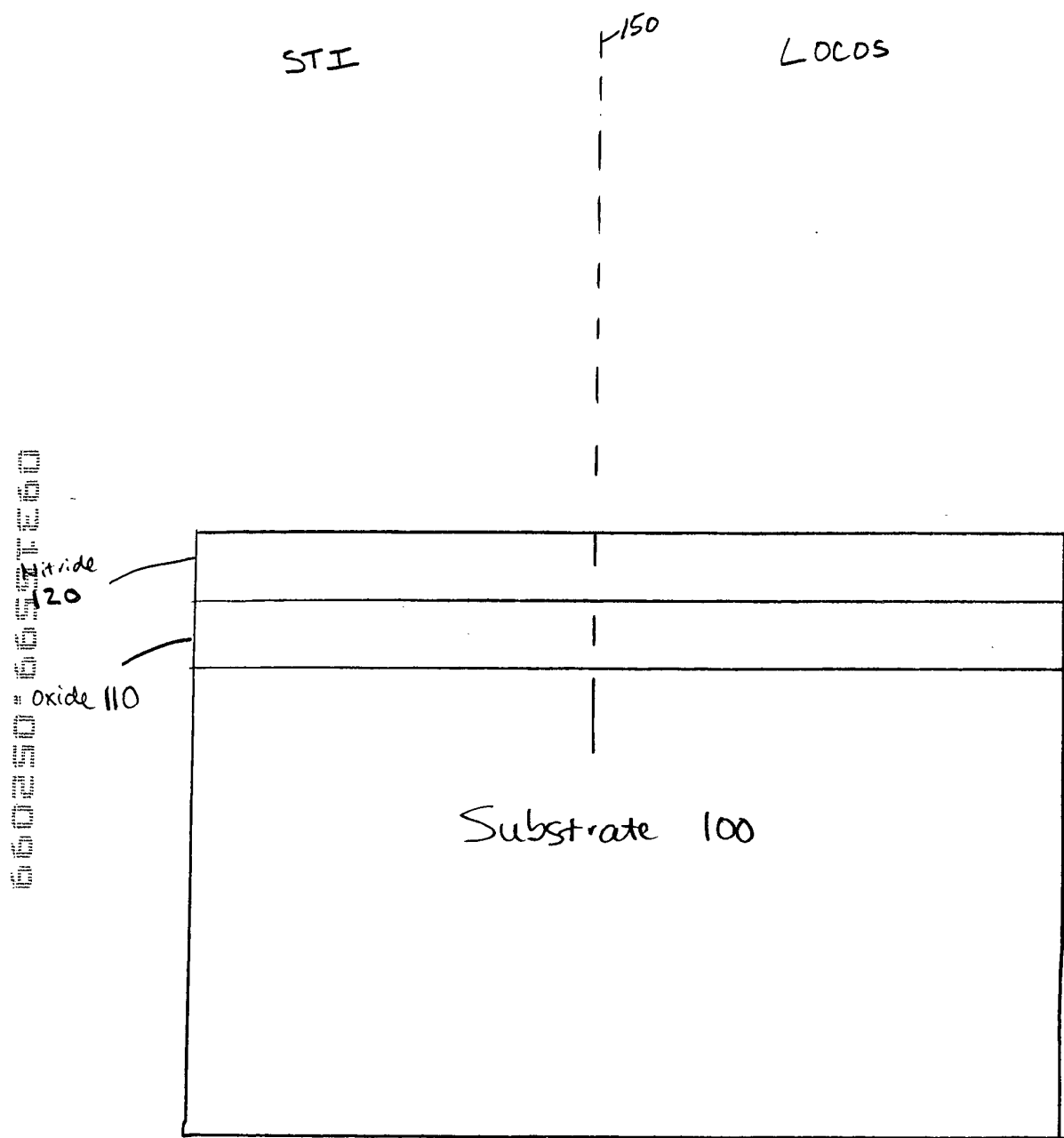


FIGURE 6

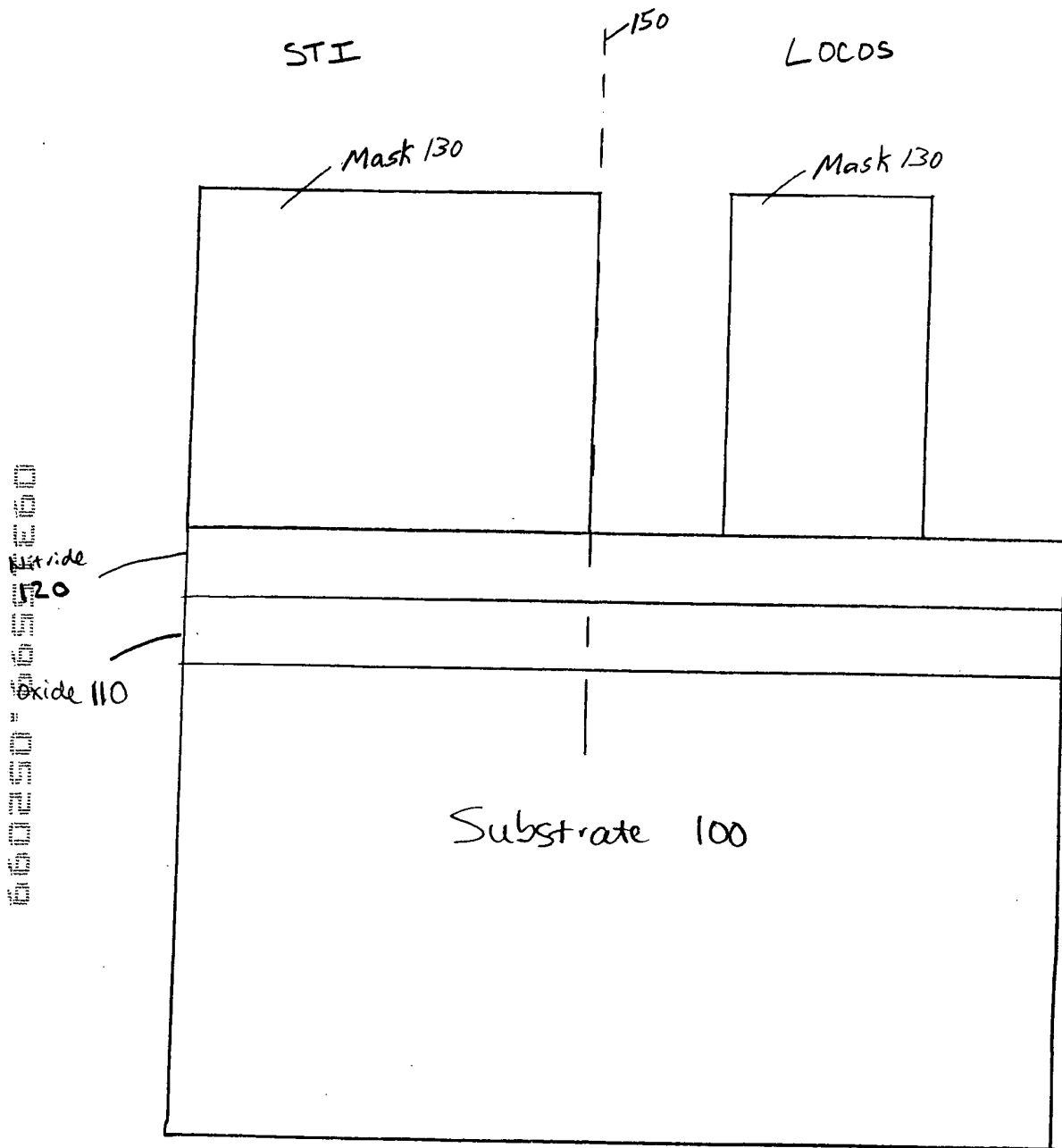


FIGURE 7

660250-665760

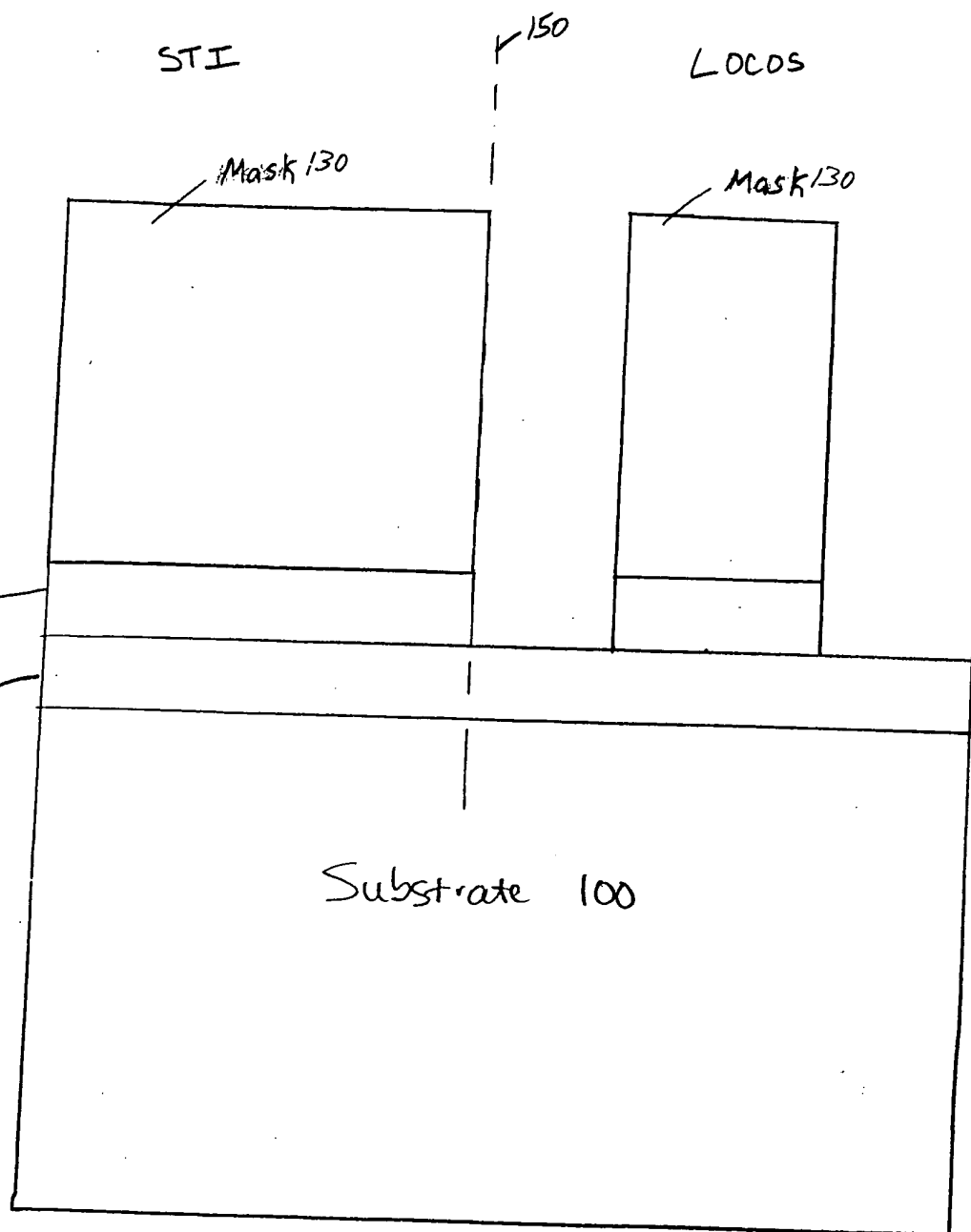


FIGURE 8

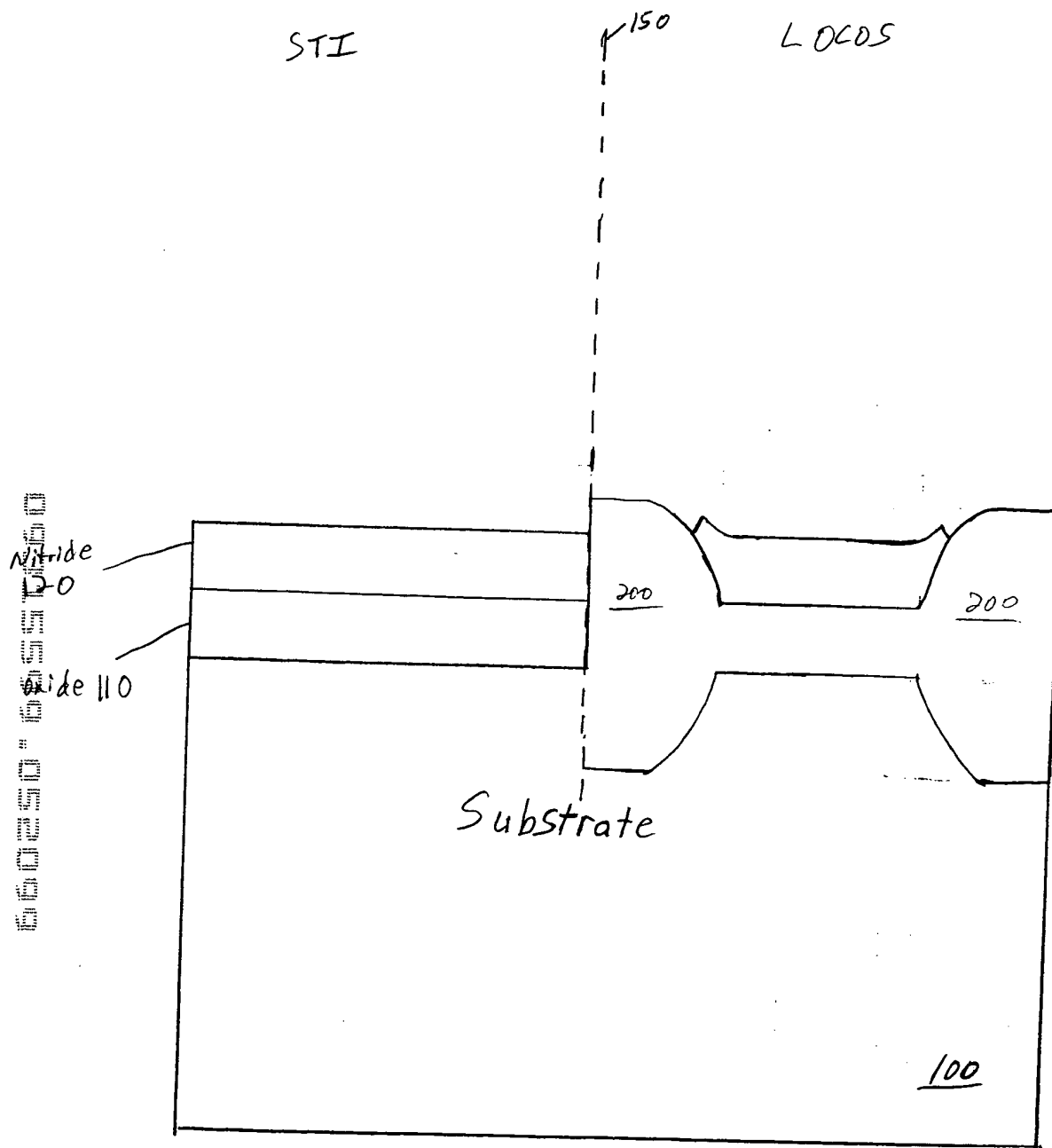


FIGURE 9

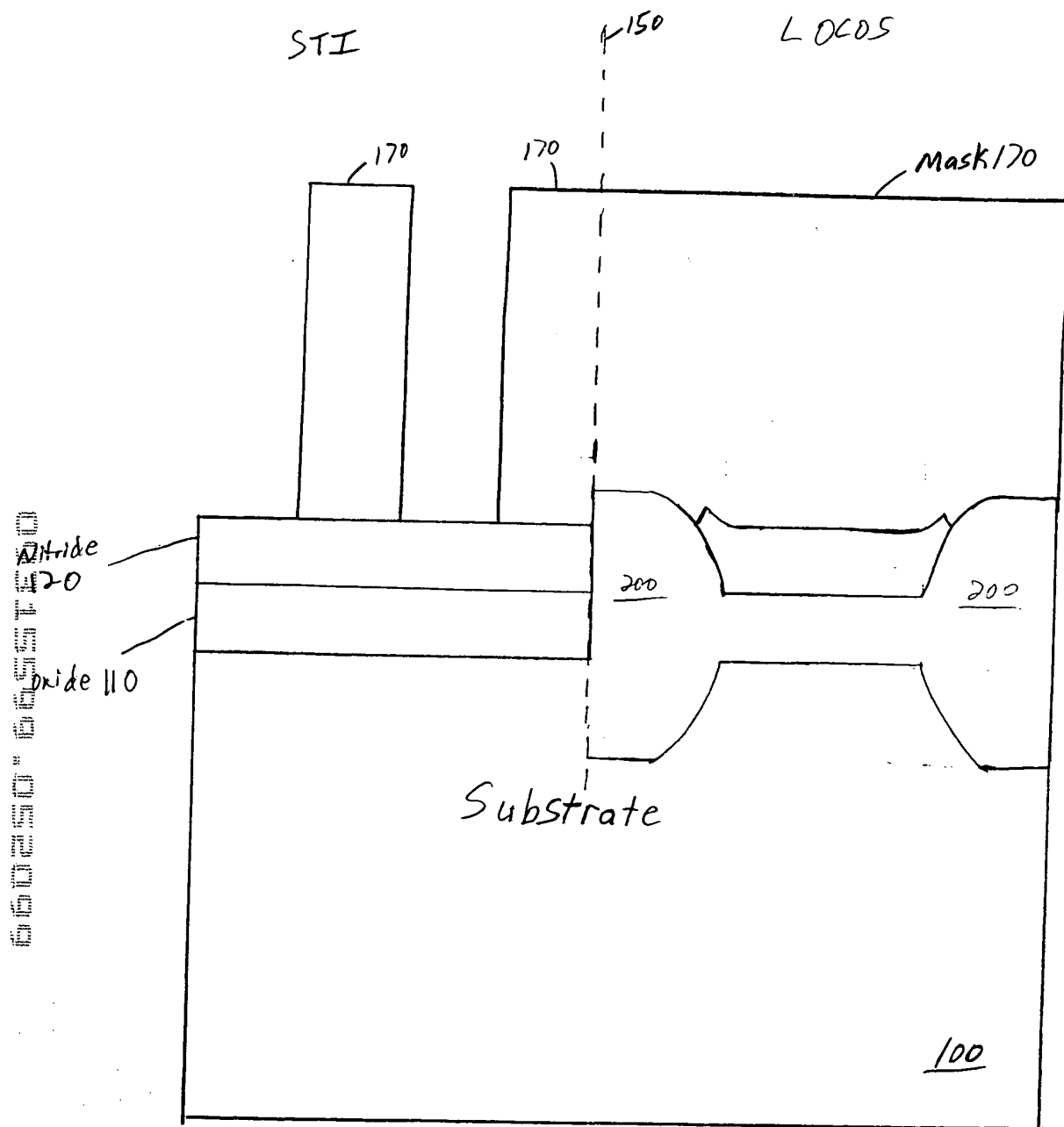


FIGURE 10

66030" 665160

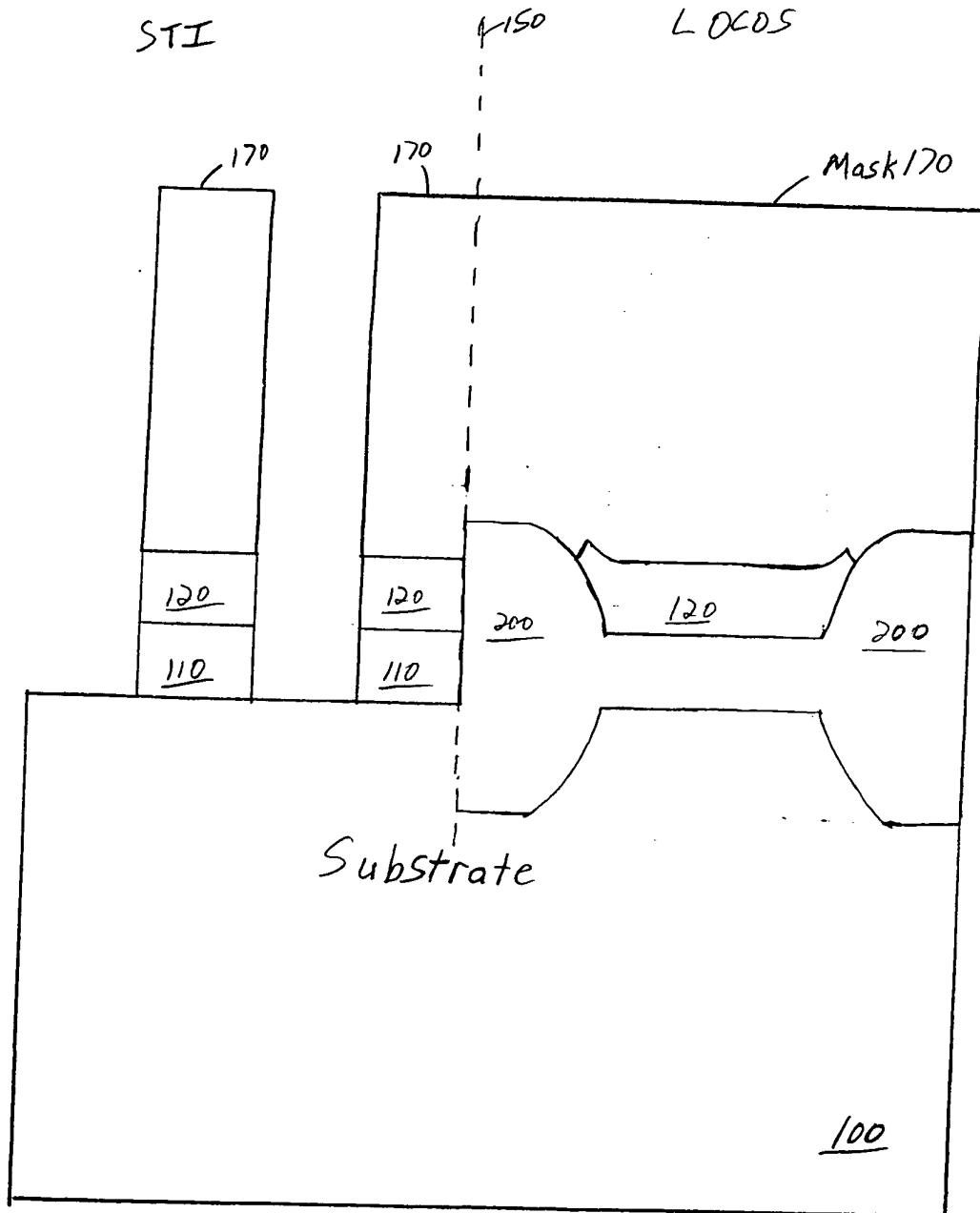


FIGURE 11

A hand-drawn cross-sectional diagram of a semiconductor device. The diagram shows a substrate (100) with a central channel region (200) and two side regions (120). The channel region is defined by a mask (170) and a substrate (100). The side regions (120) are separated from the channel by a gap (110). The top of the side regions is labeled STI (170). The bottom of the side regions is labeled LOCOS (170). The substrate is labeled Substrate (100). The channel region is labeled 200. The side regions are labeled 120. The gap is labeled 110. The mask is labeled Mask 170. The substrate is labeled 100.

FIGURE 12

60350* 60350

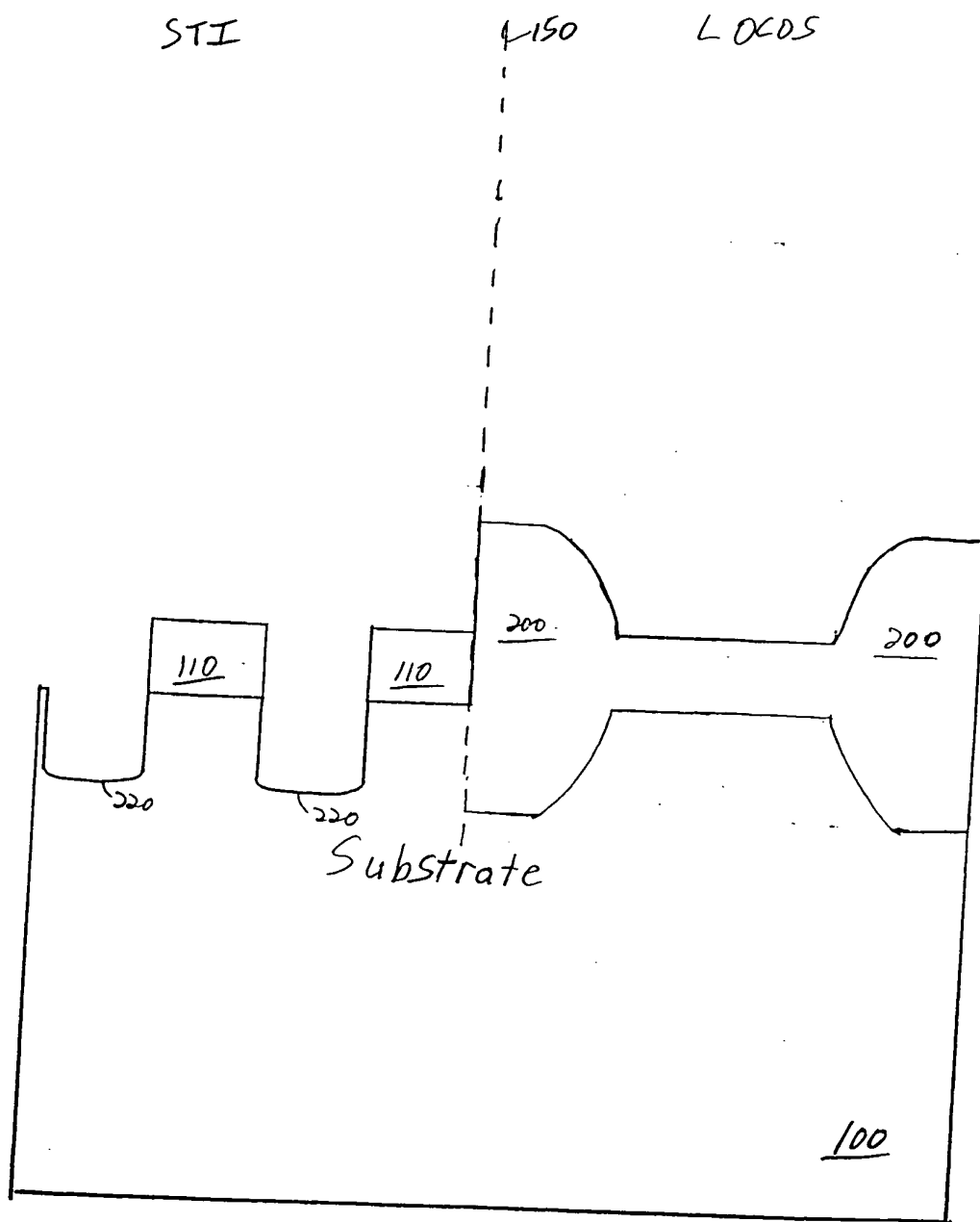


FIGURE 13

650290" 650290"

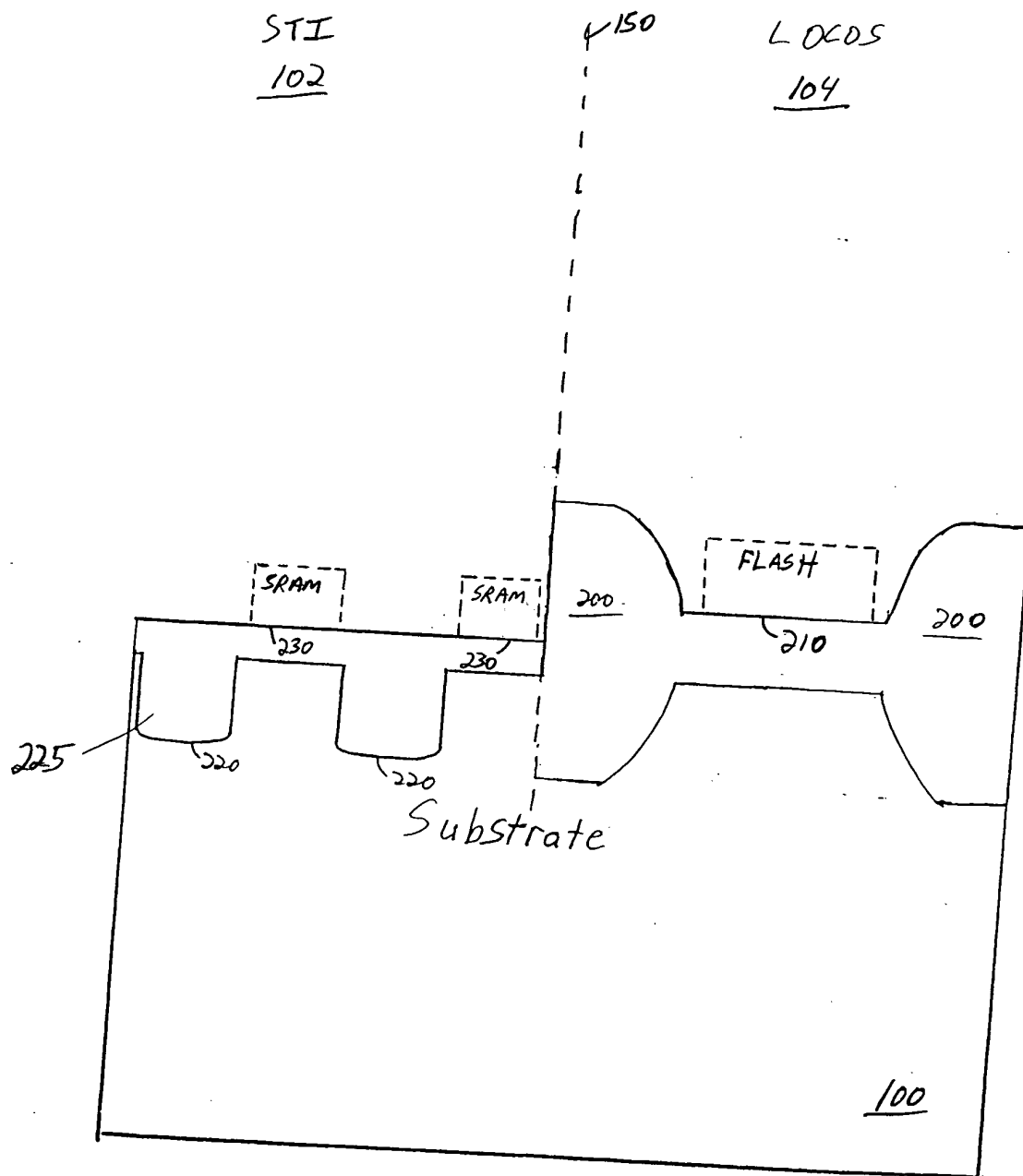


FIGURE 14